VDIC
NAND Flash Memory

VDNF32G08XS50XX4V25-Ⅱ
USER MANUAL

Version : A1

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VDIC-NAND Flash Memory

HIGH-SPEED 3.3V 4G×8bit

1. DESCRIPTION

Offered in 4Gx8bit, the VDNF32G08XS50XX4V25-II is a 32G-bit NAND Flash Memory with spare capacity of 32G -bits. The device operates at 3.3V. The I/O pins serve as the ports for address and data input/output as well as command input.

The VDNF32G08XS50XX4V25-II device is stacked with eight chips. The I/O ports and the control pins (ALE,CLE,#WE,#RE) of each chip are connected.

A program operation can be performed in typical 230μs on the (4K+224)Byte page and an erase operation can be performed in typical 700us on a (512K+28K)Byte block. Data in the data register can be read out at 25ns cycle time per Byte.

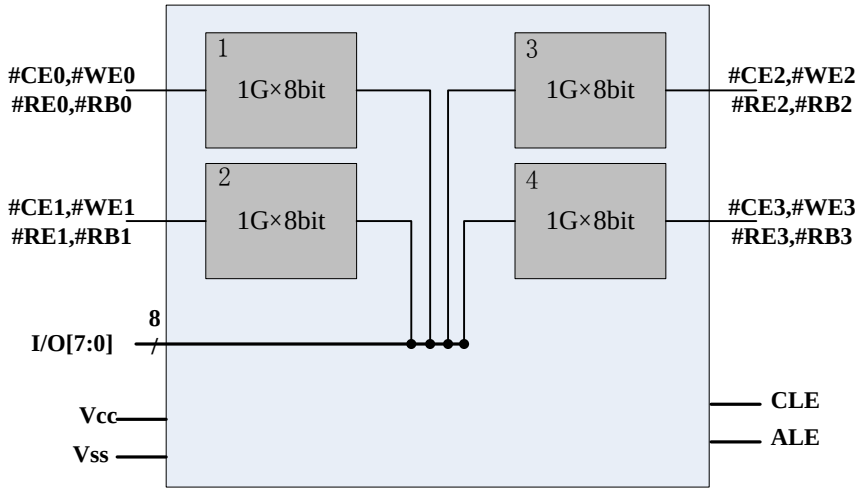
Every chip has an on-chip write controller which is used to automate all program and erase functions including pulse repetition, where required, and internal verification and margining of data. Even the write-intensive systems can take advantage of the VDNF32G08XS50XX4V25-II's extended reliability of 100K program/erase cycles by providing ECC(Error Correcting Code) with real time mapping-out algorithm.

Its NAND cell provides the most cost-effective solution for the solid state application market. The VDNF32G08XS50XX4V25-II is an optimum solution for large nonvolatile storage applications such as solid state data storage and advanced embedded control applications.

2. FEATURES

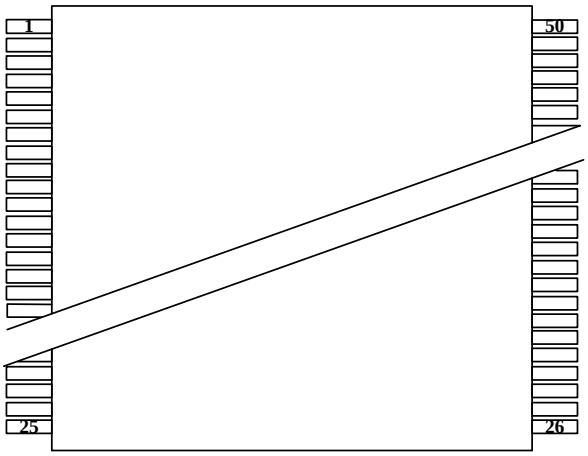
- Voltage Supply
  - 3.3V device: 2.7 ~ 3.6 V
- Organization
  - Memory Cell Array
    - 8chips x (1G +80M)x 8 bit
  - Data Register for each chip
    - (4096 +224) x 8bit
- Automatic Program and Erase
  - Page Program for each chip
    - (4K + 224)Byte
  - Block Erase for each chip
    - (512K +28K)Byte
- Page Read Operation for each chip
  - Page Size
    - (4K + 224)Byte
  - Random Access : 25μs(Max.)
  - Serial Page Access : 25ns(Min.)
- Fast Write Cycle Time
  - Program time : 230μs(Typ.)
  - Block Erase Time : 700us(Typ.)
- Command/Address/Data Multiplexed I/O Port
- Hardware Data Protection
  - Program/Erase Lockout During Power Transitions
- Reliable CMOS Floating-Gate Technology
  - Endurance : 100K Program/Erase Cycles
  - Data Retention : 10 Years
- Command Register Operation
- Intelligent Copy-Back with internal 4bit/540Byte EDC
- Package SOP-50

3. BLOCK DIAGRAM



4. PIN DESCRIPTIONS– SOP-50

Pin Id	Pin #		Pin Id
NC	1	50	**NC**
NC	2	49	**NC**
NC	3	48	**NC**
NC	4	47	**NC**
#R/B3	5	46	**#RE3**
#R/B2	6	45	**I/O7**
#R/B1	7	44	**I/O6**
#R/B0	8	43	**I/O5**
#RE0	9	42	**I/O4**
#CE0	10	41	**#RE2**
#CE1	11	40	**#RE1**
#CE2	12	39	**VCC**
VCC	13	38	**VCC**
VSS	14	37	**VSS**
#CE3	15	36	**VSS**
NC	16	35	**VSS**
CLE	17	34	**NC**
ALE	18	33	**I/O3**
#WE0	19	32	**I/O2**
#WP	20	31	**I/O1**
#WE1	21	30	**I/O0**
#WE2	22	29	**NC**
#WE3	23	28	**NC**
NC	24	27	**NC**
NC	25	26	**NC**



Name	Function
I/O0~I/O7	DATA INPUTS/OUTPUTS The I/O pins are used to input command, address and data, and to output data during read operations. The I/O pins float to high-z when the chip is deselected or when the

Name	Function
	outputs are disabled.
CLE	COMMAND LATCH ENABLE The CLE input controls the activating path for commands sent to the command register. When active high, commands are latched into the command register through the I/O ports on the rising edge of the #WE signal.
#CE0 (Chip1)	Chip Enable Input .When #CEn is Low, the command input cycle becomes valid in chip n. When #CEn is High, all inputs are ignored in chip n.
#CE1 (Chip2)	
#CE2 (Chip3)	
#CE3 (Chip4)	
ALE	ADDRESS LATCH ENABLE The ALE input controls the activating path for the address to the internal address registers. Addresses are latched on the rising edge of #WE with ALE high.
#REn	READ ENABLE The #REn input is the serial data-out control, and when active , drives the data onto the I/O bus. Data is valid t_{REA} after the falling edge of #RE which also increments the internal column address counter by one.
#WEn	WRITE ENABLE The #WEn input controls writes to the I/O port. Commands, address and data are latched on the rising edge of the #WE pulse.
#WP	WRITE PROTECT The #WP pin provides inadvertent write/erase protection during power transitions. The internal high voltage generator is reset when the #WP pin is active low.
#R/B0 (Chip1)	READY/BUSY OUTPUT The #R/Bn output indicates the status of the device operation. When low it indicates that a program, erase or random read operation is in process and returns to high state pon completion. It is an open drain output and does not float to high-z condition when the chip is deselected or when outputs are disabled.
#R/B1 (Chip2)	
#R/B2 (Chip3)	
#R/B3 (Chip4)	
VCC	POWER VCC is the power supply for device.
VSS	GROUND

5. ELECTRICAL SPECIFICATIONS

5.1. Absolute Maximum Ratings

Characteristics	Symbol	Maximum ratings	Unit
Voltage on V_{CC} supply relative to Vss	V_{CC}	-0.6 to +4.6	V
Voltage on any pin relative to Vss	V_{IN}	-0.6 to +4.6	V
Power Dissipation	P_D	<1.5	W
Operating Temperature Range	T_A	-55~ +125	℃
Storage Temperature Range	T_{STG}	-65 to +150	℃

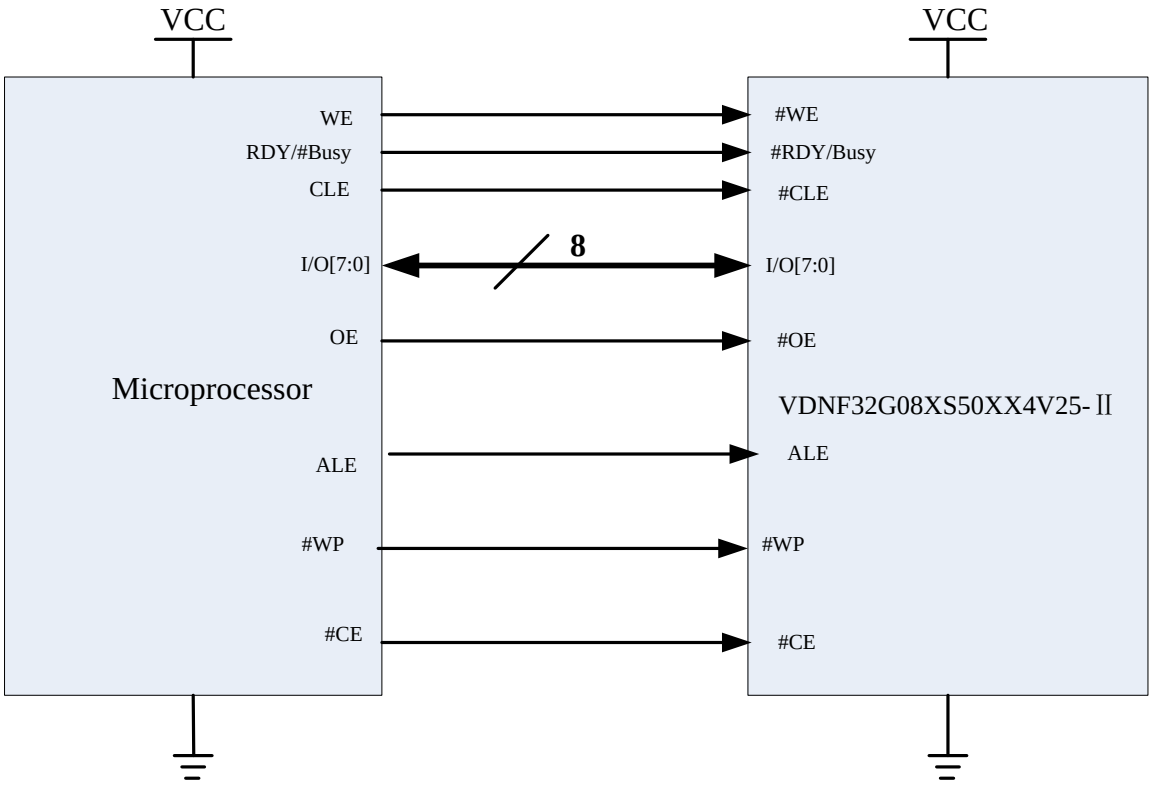
5.2. Recommended DC Operating Conditions

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	2.7	3.3	3.6	V
Input high voltage	V_{IH}	V_{CC}×0.8	——	V_{CC}+0.3	V
Input low voltage	V_{IL}	-0.3	——	V_{CC}×0.2	V

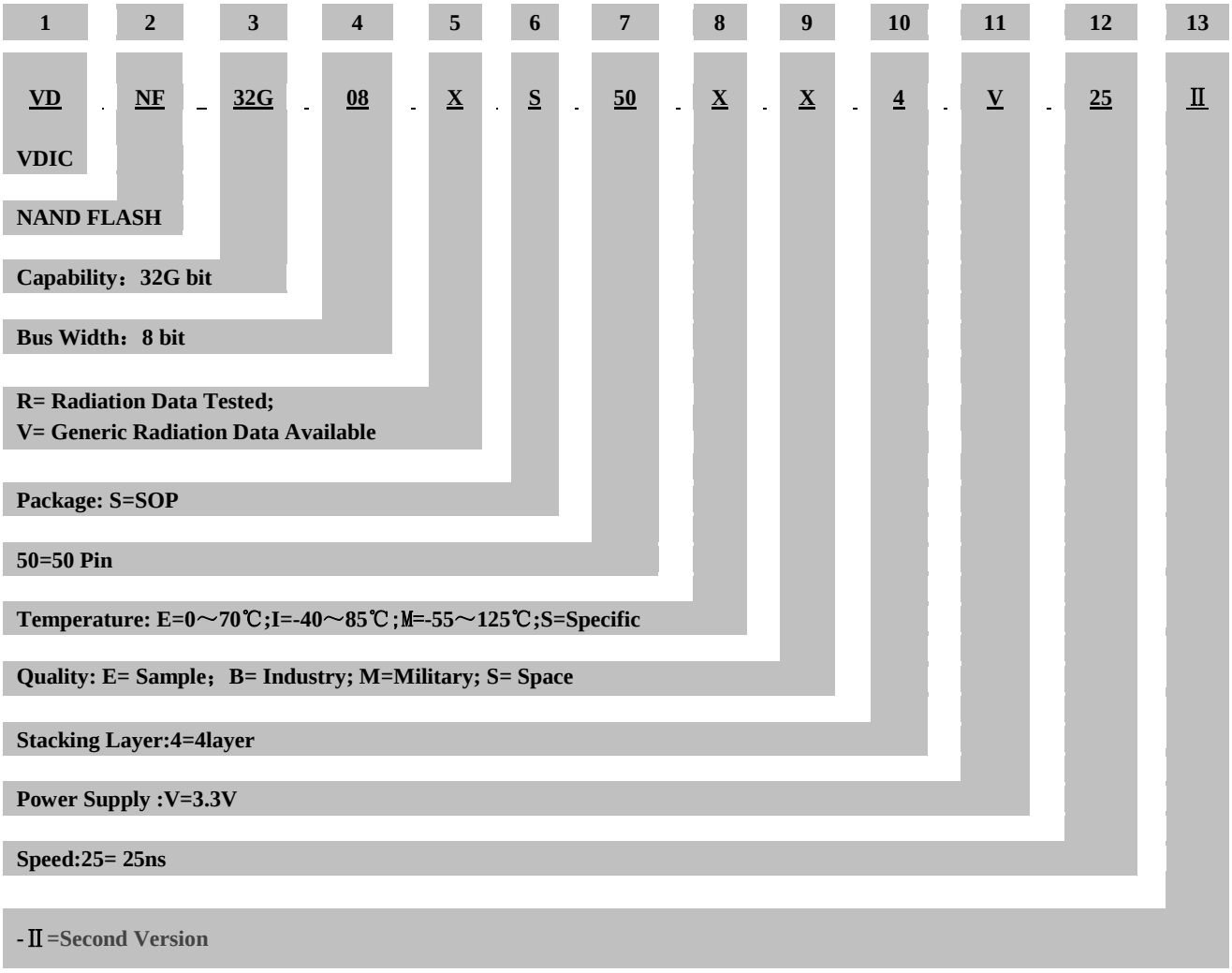
5.3. DC And Operating Characteristics

Parameter	Symbol	Test Conditions	Min	Max	Unit
Output voltage low level	V_{OL}	V_{CC}=2.7V I_{OL} =2.1mA	——	0.4	V
Output voltage high level	V_{OH}	V_{CC}=2.7V,I_{OH}= -0.4mA	2.4	——	V

6. Typical Application



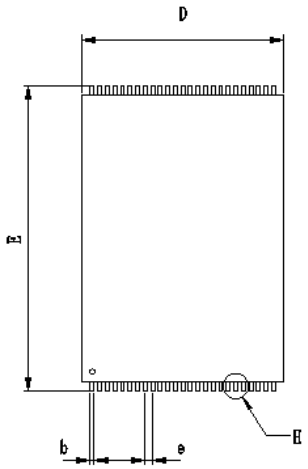
7. ORDERING INFORMATION



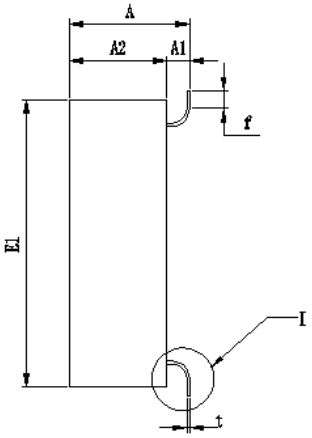
Part Number	Capacity (bit)	Bus Width (bit)	Radiation			Packaging	Temperature (℃)
			TID[1]	SEL[2]	SEU[3]		
VDNF32G08VS50EE4V25-Ⅱ	32G	8	-	-	-	SOP50	0 ~ +70
VDNF32G08VS50IB4V25-Ⅱ	32G	8	-	-	-	SOP50	-40 ~ +85
VDNF32G08VS50MB4V25-Ⅱ	32G	8	-	-	-	SOP50	-55 ~ +125
VDNF32G08VS50MM4V25-Ⅱ	32G	8	-	-	-	SOP50	-55 ~ +125
VDNF32G08RS50MS4V25-Ⅱ	32G	8	>60	>62.5	1.3	SOP50	-55 ~ +125

[1] TID: Total Dose（Krads(Si)）
[2] SEL: LET Threshold（Mev.cm2/mg）
[3] SEU:SEU Threshold （Mev.cm2/mg）

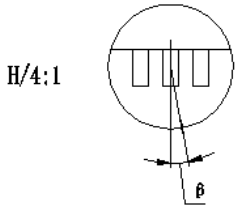
8. PACKAGE DIMENSIONS

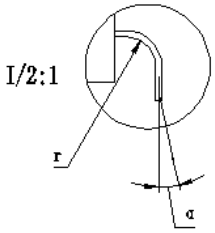


TOP VIEW



SIDE VIEW





	Min	Max
A	7.40	7.90
A2	6.20	6.60
D	13.30	13.70
E	19.80	20.20
E1	18.80	19.20
f	1.20	
b	0.25	
e	0.50	
r	1.00	
t	0.20	
α	≤3°	
β	≤3°	
NOTE：1. Unit：mm 2. A1= A - A2		

9. REVISION HISTORY

Revision	Date	Description of Change
A0	Jun 3,2017	First Created
A1	Mar 29,2018	Add or reduce chapters